PTO/SB/08A (10-01)
Approved for use through 10/31/2002, OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known	
Application Number	10/624,384
Filing Date	July 22, 2003
First Named Inventor	Leybovich
Art Unit	1753
Examiner Name	VerSteeg
Attorney Docket Number	020324 227P2

Sheet 1 of 3

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Class	Subclass
SHV	AA	US-6,395,649	05-28-2002	Wu, Hui-Jung	438		778
SHV	AB	US-6,340,435	01-22-2002	Bjorkman et al.	216		72
	AC	US-					
	AD	US-					
	AE	US-					
	AF	US-					
	AG	US-					
	AH	US-					
	AI	US-					

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document Country - Number[4] -KindCode[5] Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

Examiner Signature		Date Considered	March 17, 2005

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
[1]Applican'ts unique citation designation number (optional). [2]See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04.
[3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached.
Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Office, U.S. Patent and Trademark Office, Washington, DC20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant commissioner for Patents, Washington, DC 20231.

PTO/SB/08A (10-01)
Approved for use through 10/31/2002, OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/624,384
				Filing Date	July 22, 2003
				First Named Inventor	Leybovich
				Art Unit	1753
				Examiner Name	Ver Steeg
Sheet	2	of	3	Attorney Docket Number	020324 227P2

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the auther (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
SHV	AJ	BALIGA, J.; Low-k Dielectrics Enable Faster Chips, Design News: Semiconductor Manufacturing, June 3, 2002, pp. S/13-S14	
SHV	AK	CHAPMAN, B.; DC Glow Discharges, pp. 98-101	
SHV	AL	THOMAS, MICHAEL E.; Spin-On Stacked Films for Low-k_{eff} Dielectrics, Solid State Technology, July 2001, pp. 105-113	
SHV	AM	MAISSEL, Leon and GLANG, Reinhard; Handbook of Thin Film Technology, pp. 3-14—30-15, 3-24—3-27, 4-26—4-37, McGraw Hill Book Company	
SHV	AN	SHIMOKAWA, F. and KUWANO, K; New High-Power Fast Atom Beam Source, J. Vac. Sci. Technol. A 12(5), Sep./Oct. 1994, pp. 2739-2744	
SHV	AO	ONO T., ORIMOTO, H., LEE S., SIMIZU, T. and ESASHI, M.; RF-Plasma Assisted Fas Atom Beam Etching, Jpn. J. Appl. Phys. Vol. 39 (2000) pp. 6976-6979, Part I, No. 12B, December 2000	
SHV	AP	SHIMOKAWA, F.; High-Power Fast-Atom Beam Source and Its Application to Dry Etching, J. Vac. Sci. Technol. A10(4), July/Aug. 1992, pp. 1352-1357	
SHV	AQ	SHIMOKAWA, F. and KUWANO H., New High-Power Fast Atom Beam Source, J. Vac. Sci. Technol. A12(5), Sept/Oct 1994, pp. 2739-2744	
SHV	AR	SHIMOKAWA, F. and NAGAI, K.; A Low-Energy Fast-Atom Source, Nuclear Instruments and Methods in Physics Research B33 (1988) pp. 867-870	
SHV	AS	SHIMOKAWA, F., KUWANO, H. and NAGAI, K.; Energy Distribution of Fast Atom Beam Produced by an Fab Source, Proc. 10th Symp. On ISIAT '86, Tokyo (1986) pp. 101-104	
SHV	AT	BEHRISCH, R.; Sputtering By Particle Bombardment I: Physical Sputtering of Single-Element Solids; Springer-Verlag Berlin Heidelberg New York 1981. pp. 200-203	

March 17, 2005

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/624,384
				Filing Date	July 22, 2003
(use as many sheets as necessary)				First Named Inventor	Leybovich
				Art Unit	1753
				Examiner Name	Ver Steeg
Sheet	3	of	3	Attorney Docket Number	020324 227P2

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the auther (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[2]
SHV	AU	GORBATOV, Y., VYATKIN, A. and ZINENKO, V.; A Low-Energy Fast-Atom Beam Source, Nuclear Instruments and Methods in Physics Research B55 (1991) 328-330	
SHV	AV	Sputter Etching and Deposition of Insulators, pp. 195-197	
SHV	AW	CHAPMAN, B.; Glow Discharge Processes, Sputtering and Plasma Etching, pp. 38-41, John Wiley & Sons (1980)	
SHV	AX	CHEUNG et al.; Integration and Characterization of Low Carbon Content SiO/subx/C/suby/H/subz/ Low K Materials for <0.18 mu m Dual Damscene Application; Materials Research Society Symposium Proceedings, Vol. 612, 2000 (Abstract)	
SHV	AY	MOUNTSIER et al.; Integration Studies of Plasma Deposited Flouorinated Amorphous Carbon, Low-Dielectric Constant Materials IV Symposium, pp. 259-64 1998 (Abstract)	
SHV	AZ	MOUNTSIER, T. and SAMUELS, J.; Precursor Selection for Plasma Deposited Flourinated Amorphous Carbon Films; Thin Solid Films (Switzerland) Vol. 332, 2 Nov. 1998 (Abstract)	
SHV	BA	YU et al.; Low K Film Etch in Applied Materials eMxP Plus Chamber; Materials Research Society Symposium – Proceedings, 1999 (Abstract)	
SHV	BB	ZHANG et al.; Nanoglass/sup TM/E Copper Damascene Processing for Etch, Clean, and CMP; Proceedings of the IEEE 2001 International Interconnect Technology Conference 2001, pp. 57-9 (Abstract)	
SHV	BC	BARSKAYA, A. YA. et al; Sputtering of Different Materials by Ions and Atoms, Journal of Technical Physics, v57, 6, 1987, pp 1223-1225 (Accompanied with two English abstracts)	

Examiner Signature		Date Considered	March 7, 2005